

ABSTRACT OF THE DISCLOSURE

A semiconductor device comprises a semiconductor substrate, a first circuit formed on the substrate, and a second circuit connected to the first circuit as an input/output portion thereof and powered by a voltage higher than that for the first circuit, the first circuit including a first and a second field-effect transistor, the first drain region of the first transistor accompanying a first load capacitance, the second drain region of the second transistor accompanying a second load capacitance smaller than the first load capacitance, and the first gate insulation film of the first transistor having an average relative dielectric constant higher than that of the second gate insulation film of the second transistor, thereby realizing a high operation speed.